

Clean version of the claims:

Please add claims 18-22, as follows:

18. (New) A semiconductor device, comprising:
 - a common substrate;
 - a first region formed on the common substrate, the first region comprising an SRAM device, a first active region, and a first isolation region having a first isolation structure, the SRAM device overlying the first active region, the first active region isolated by the first isolation region, the first active region and the first isolation region forming a uniform region made of a first material; and
 - a second region formed on the common substrate, the second region comprising a flash EPROM device, a second active region, and a second isolation region having a second isolation structure, the flash EPROM device overlying the second active region, the second active region isolated by the second isolation region, the second active region and the second isolation region forming a uniform region made of a second material,wherein the first isolation structure is different from the second isolation structure.
19. (New) The semiconductor device of claim 18, wherein the first isolation structure is a shallow trench.
20. (New) The semiconductor device of claim 18, wherein the second isolation structure is a LOCOS isolation structure.
21. (New) The semiconductor device of claim 18, wherein the first material comprises an insulating oxide.
22. (New) The semiconductor device of claim 18, wherein the second material comprises an insulating oxide.